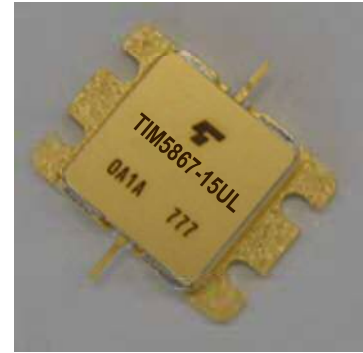


**FEATURES**

- **BROAD BAND INTERNALLY MATCHED FET**
- **HIGH POWER**  
P1dB= 42.0dBm at 5.85GHz to 6.75GHz
- **HIGH GAIN**  
G1dB= 10.0dB at 5.85GHz to 6.75GHz
- **LOW INTERMODULATION DISTORTION**  
IM3(MIN.)= -42dBc at Pout= 31dBm (Single Carrier Level)
- **HERMETICALLY SEALED PACKAGE**



**RF PERFORMANCE SPECIFICATIONS ( Ta= 25°C )**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 3.2A f= 5.85 to 6.75GHz	dBm	41.0	42.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	9.0	10.0	—
Drain Current	IDS1		A	—	3.5	4.0
Gain Flatness	ΔG		dB	—	—	±0.8
Power Added Efficiency	ηadd		%	—	41	—
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 31dBm, Δf= 5MHz (Single Carrier Level)	dBc	-42	-47	—
Drain Current	IDS2		A	—	3.5	4.0
Channel Temperature Rise	ΔTch	(VDS × IDS + Pin - P1dB) × Rth(c-c)	°C	—	—	80

**Recommended Gate Resistance(Rg): 68 Ω**

**ELECTRICAL CHARACTERISTICS ( Ta= 25°C )**

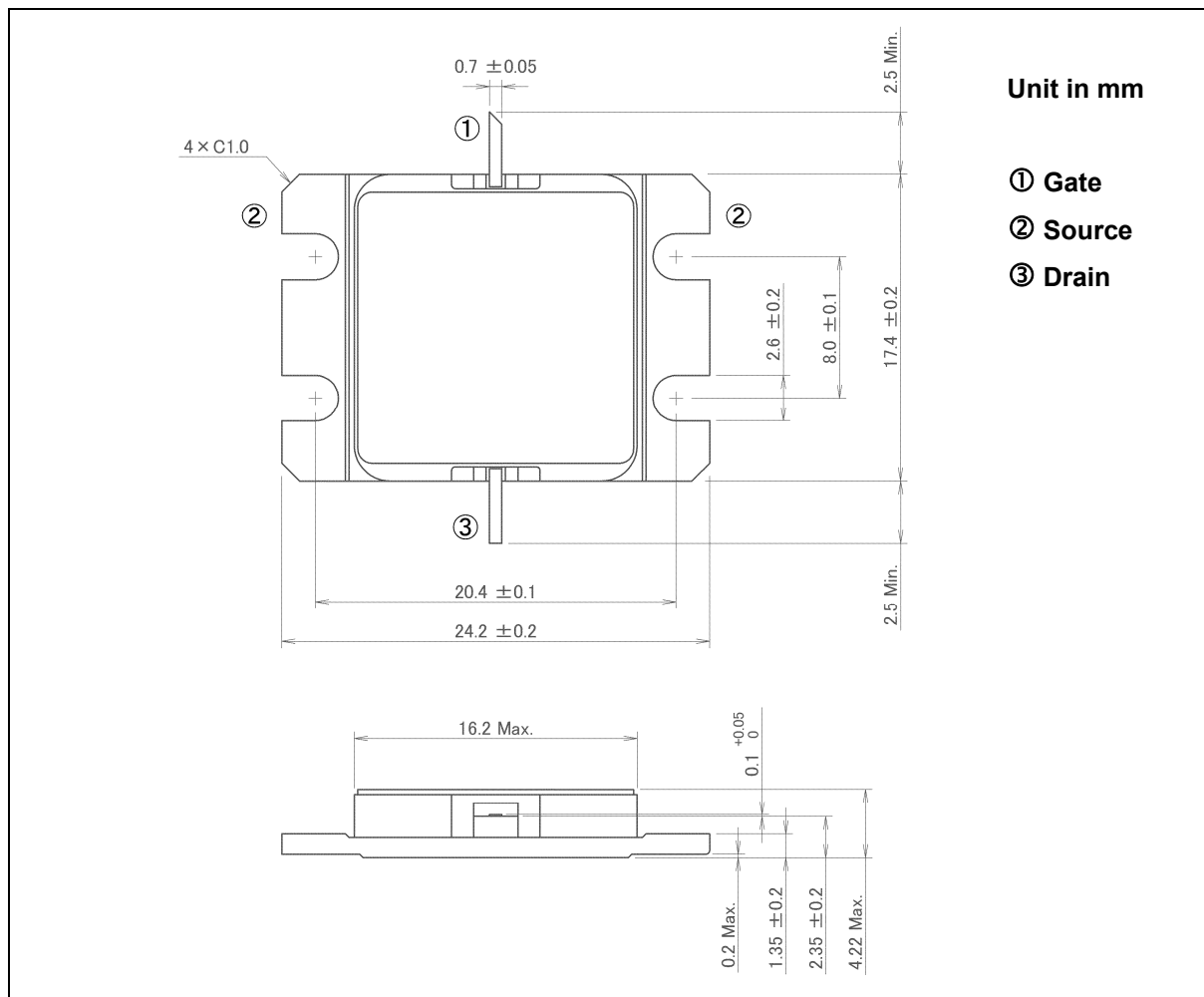
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 5.0A	S	—	4.0	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 40mA	V	-0.5	-2.0	-3.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	8.0	—
Gate-Source Breakdown Voltage	VGSO	IGS= -120μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	2.0	2.4

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**ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)**

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	12.0
Total Power Dissipation (Tc= 25 °C)	PT	W	62.5
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

**PACKAGE OUTLINE (2-16G1B)**



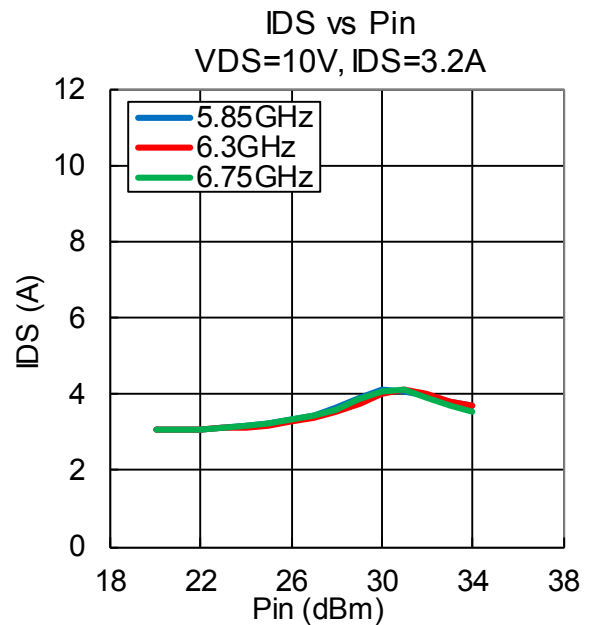
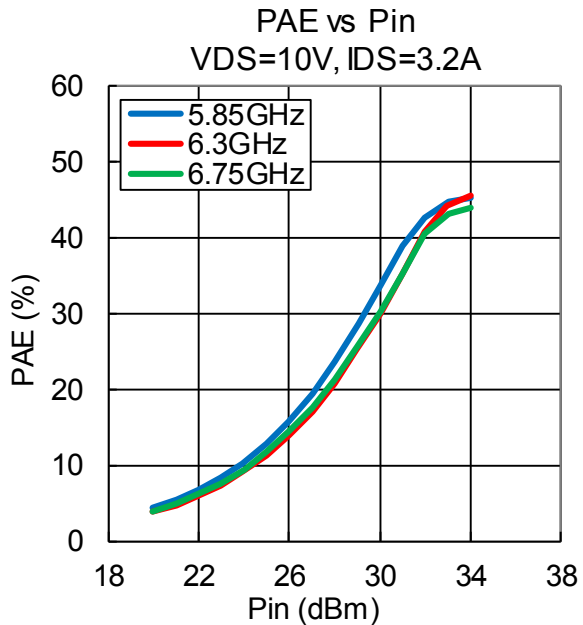
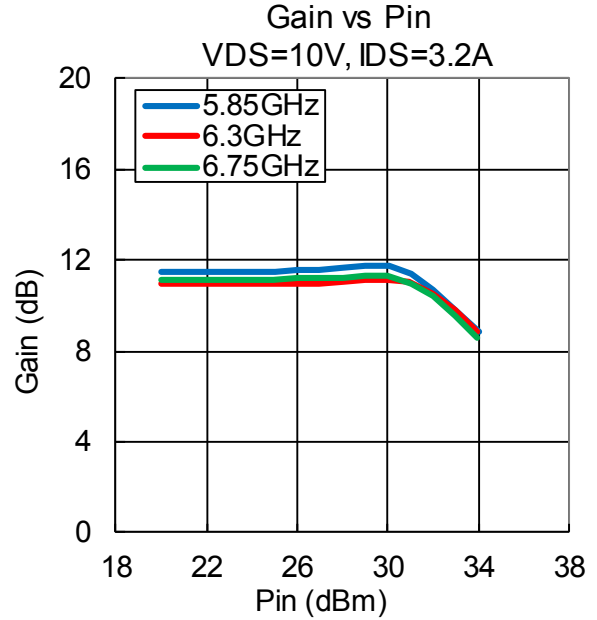
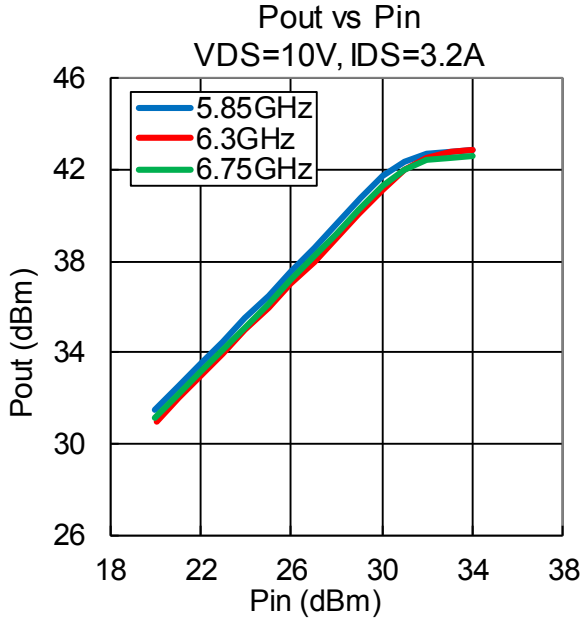
**HANDLING PRECAUTIONS FOR PACKAGE MODEL**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

**TYPICAL RF PERFORMANCE**

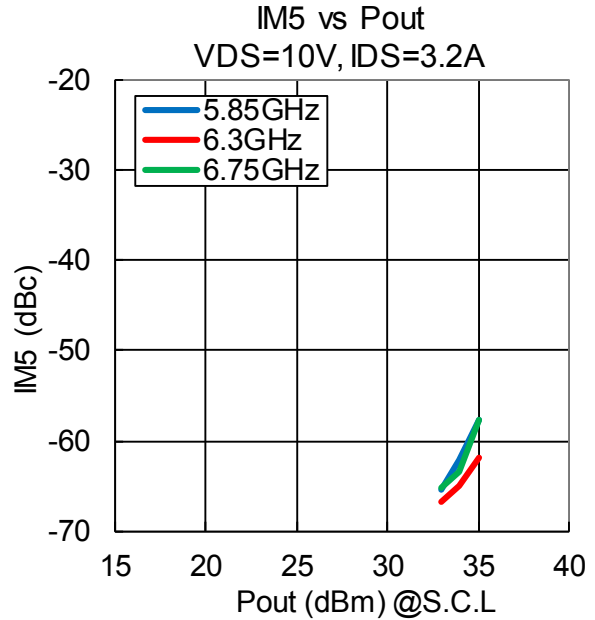
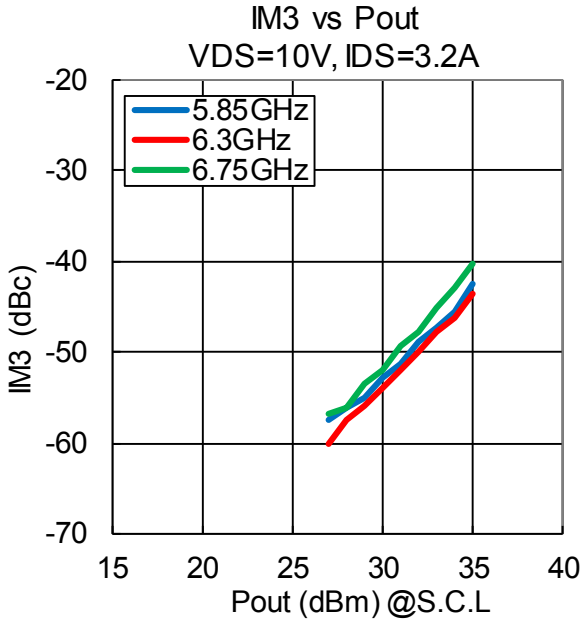
• Pout , Gain , PAE , IDS vs. Pin

VDS= 10 V, IDSset= 3.2 A, f= 5.85, 6.3, 6.75 GHz, Ta= +25 °C



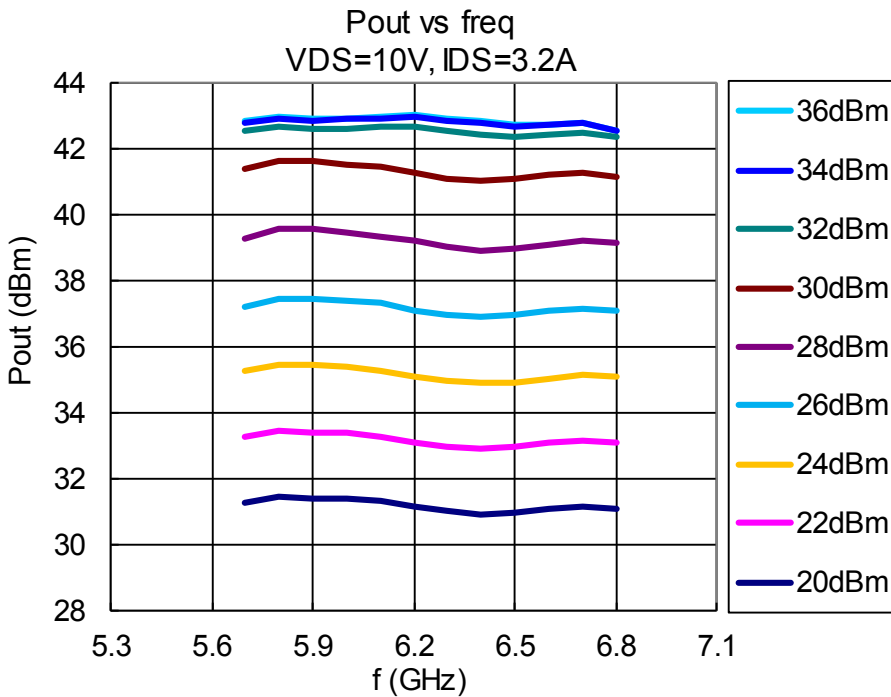
**•IM3, IM5 vs. Pout**

VDS= 10 V, IDSset= 3.2 A, f= 5.85, 6.3, 6.75 GHz, Δf= 5 MHz, Ta= +25 °C



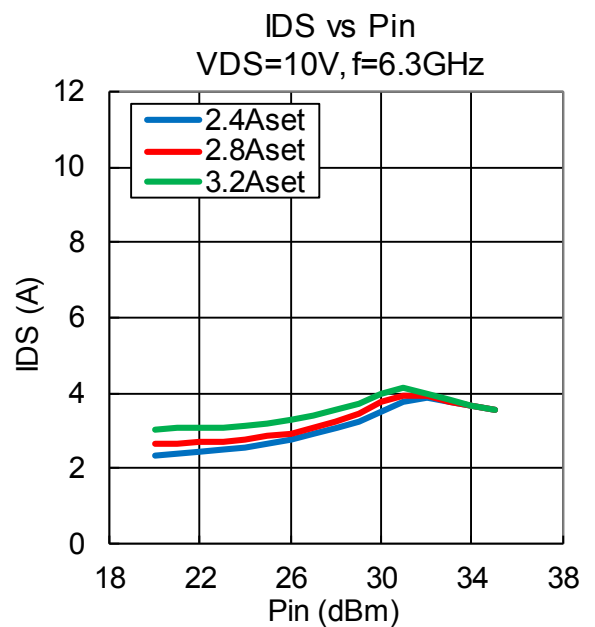
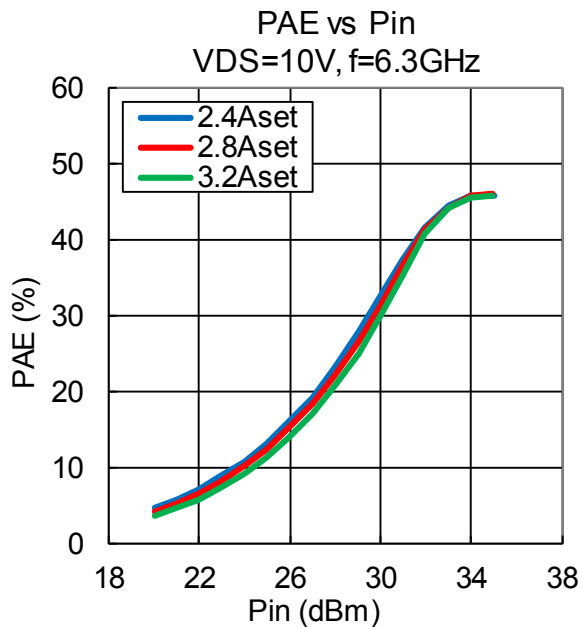
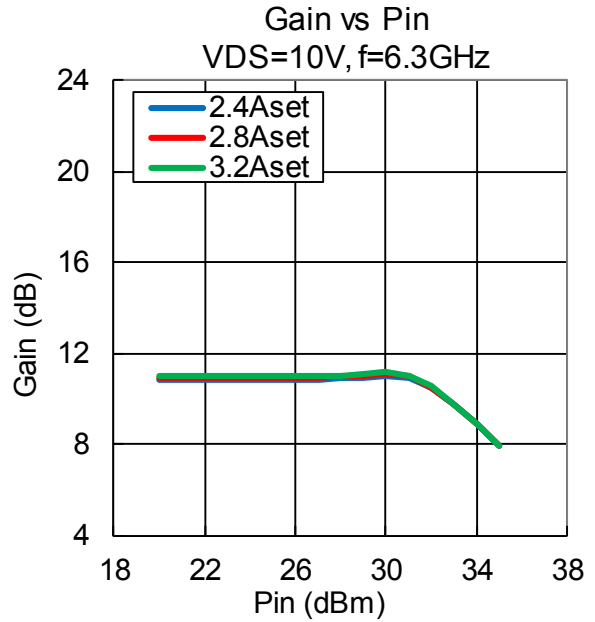
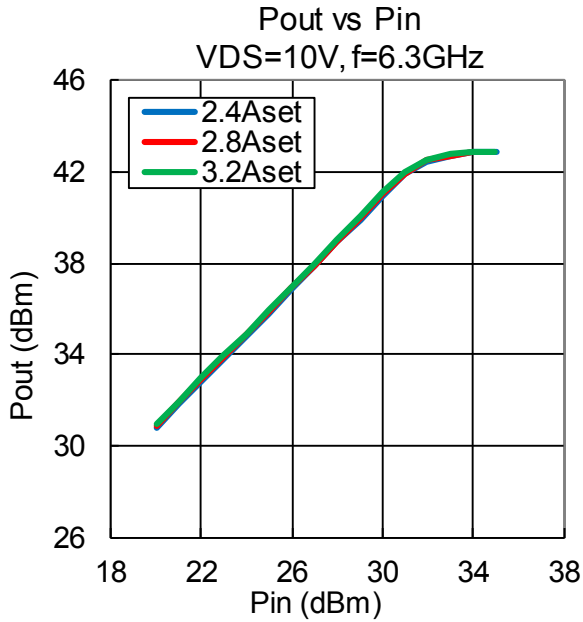
**•Pout vs. Frequency**

VDS= 10 V, IDSset= 3.2 A, Ta= +25 °C



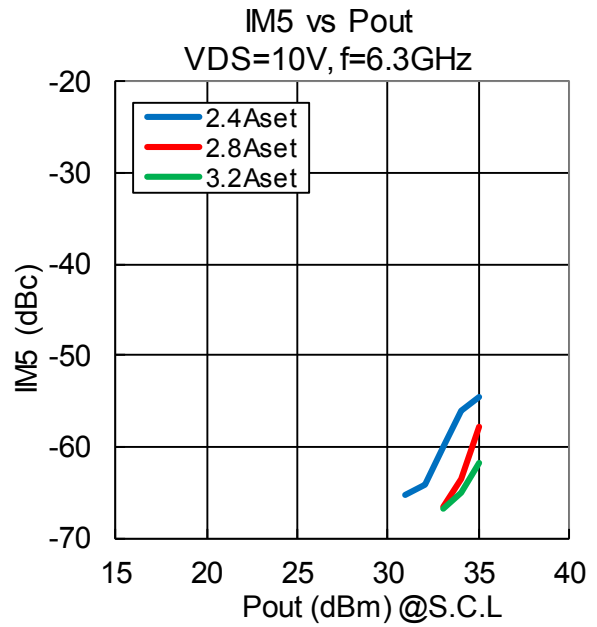
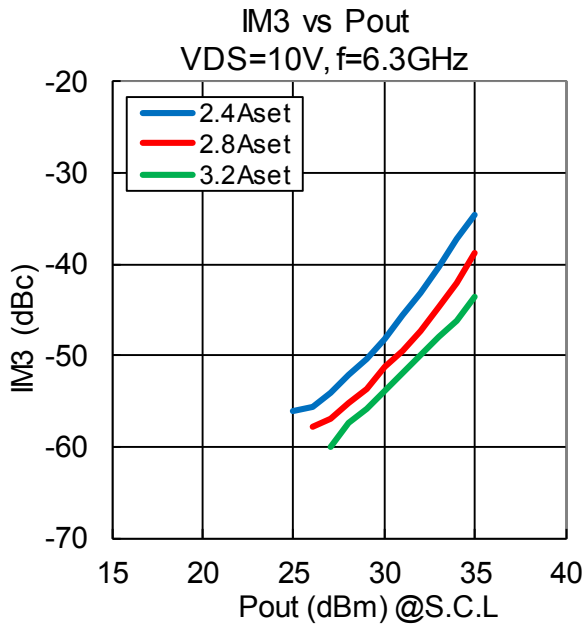
•Pout , Gain , PAE , IDS vs. Pin

VDS= 10 V, IDSset= 2.4, 2.8, 3.2 A, f= 6.3 GHz, Ta= +25 °C



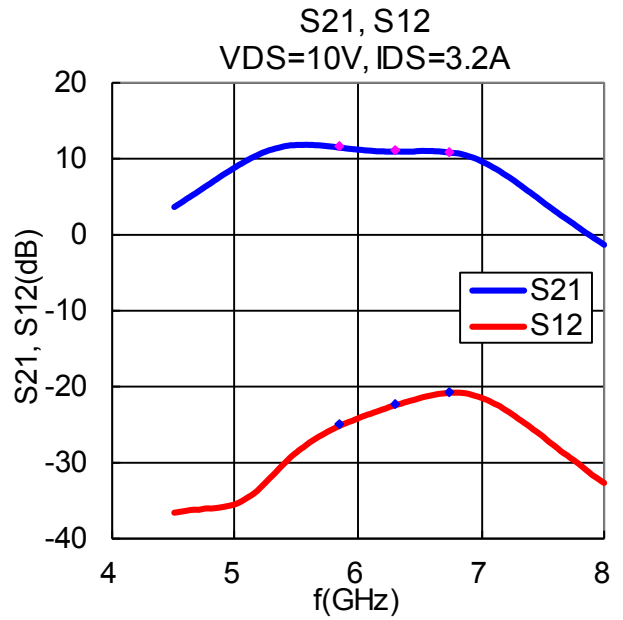
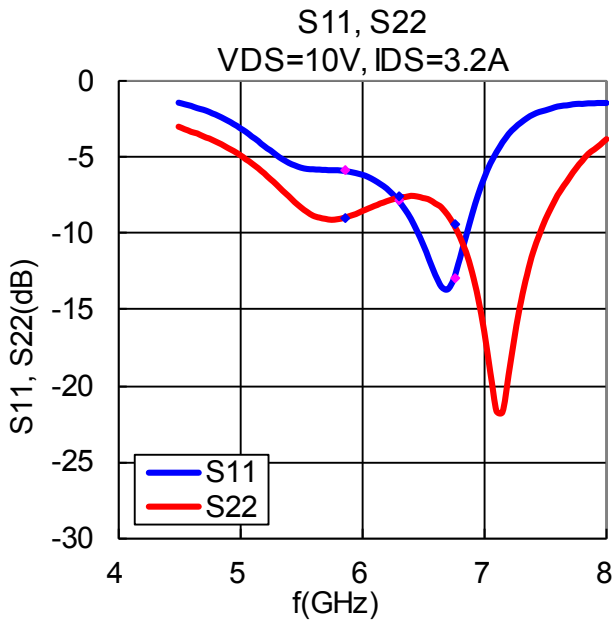
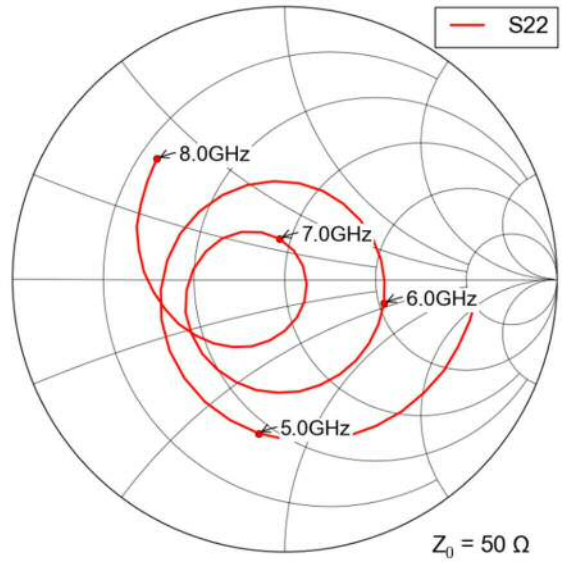
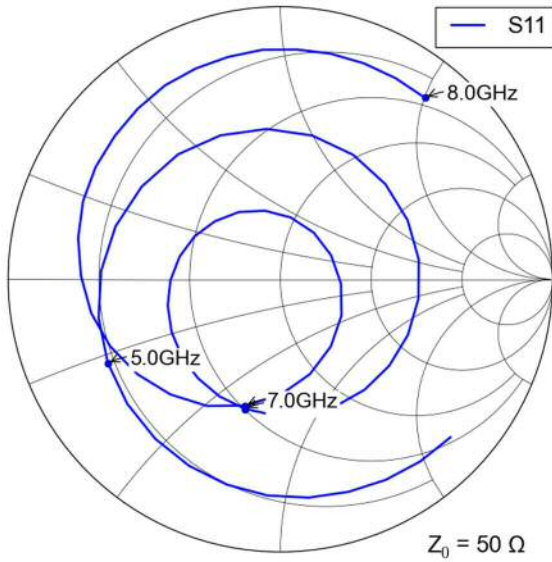
•IM3, IM5 vs. Pout

VDS= 10 V, IDSset= 2.4, 2.8, 3.2 A, f= 6.3 GHz, Δf= 5 MHz , Ta= +25 °C



**-S-Parameters**

VDS= 10 V, IDSset= 3.2 A, f= 4.5 to 8.0 GHz, Ta= +25 °C



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